NPN Planar Silicon Darlington Transistor

[2SC3987]

10.0

Package Dimensions

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2 55

unit:mm

2041A



2SC3987

Driver Applications

1 : Base

2 : Collector 3 : Emitter

SANYO : TO-220ML

Applications

• Suitable for use in switching of L load (motor drivers, printer hammer drivers, relay drivers).

Features

- · High DC current gain.
- · Large current capacity and wide ASO.
- \cdot On-chip Zener diode of 60±10V between collector and base.
- Uniformity in collector-to-base breakdown voltage due to the adoption of an accurate impurity diffusion process.
- · High inductive load handling capability.
- · Micaless package facilitating mounting.

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter Symbol Conditions Ratings Unit 50* Collector-to-Base Voltage V_{CBO} V Collector-to-Emitter Voltage 50* V VCEO Emitter-to-Base Voltage 6 V V_{EBO} Collector Current 3 А ΙC Collector Current (Pulse) 6 А **I**CP Base Current 0.6 А ΙB 2.0 W $^{\mathsf{P}}\mathsf{C}$ **Collector Dissipation** Tc=25°C 20 W Tj °C 150 Junction Temperature °C Storage Temperature Tstg -55 to +150

* : With Zener diode (60±10V)

Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions		Unit				
	Symbol		min	typ	max			
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0			10	μA		
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0			2	mA		
DC Current Gain	hFE	V _{CE} =5V, I _C =1.5A	1000	4000				
Gain-Bandwidth Product	fT	V _{CE} =5V, I _C =1.5A		180		MHz		
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1.5A, I _B =6mA		1.0	1.5	V		
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1.5A, I _B =6mA			2.0	V		
Continued on next pas								

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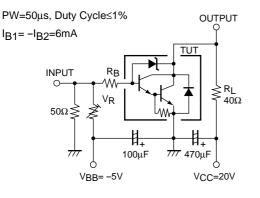
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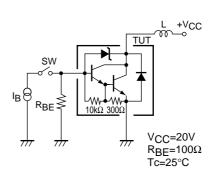
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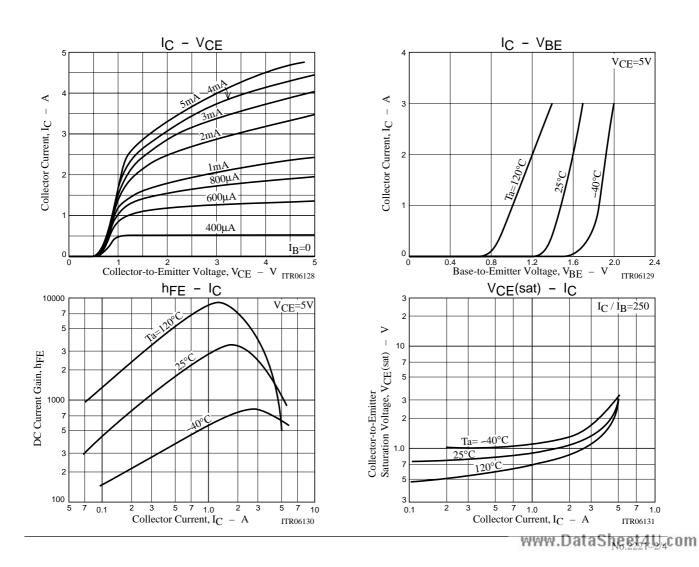
	Parameter	Symbol	Conditions	Ratings			Unit
	Falameter	Symbol		min	typ	max	Unit
www.da	Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =0.1mA, I _E =0	50	60	70	V
	Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =1mA, R _{BE} =∞	50	60	70	V
	Inductive Load Handling Capability	Es/b	L=100mH, R _{BE} =100Ω	30			mJ
	Turn-ON Time	ton	See specified Test Circuit. $V_{CC}=20V$, $I_{C}=1.5A$, $I_{B1}=-I_{B2}=6mA$		0.2		μs
	Storage Time	^t stg	See specified Test Circuit. $V_{CC}=20V$, $I_C=1.5A$, $I_{B1}=-I_{B2}=6mA$		3.0		μs
	Fall Time	t _f	See specified Test Circuit. V_{CC} =20V, I _C =1.5A, I _{B1} =-I _{B2} =6mA		0.7		μs

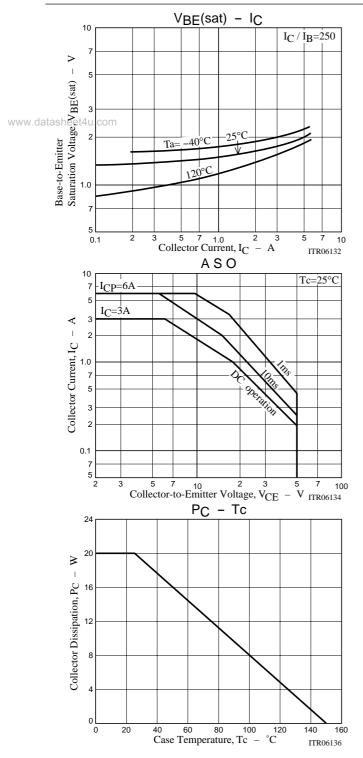
Switching Time Test Circuit

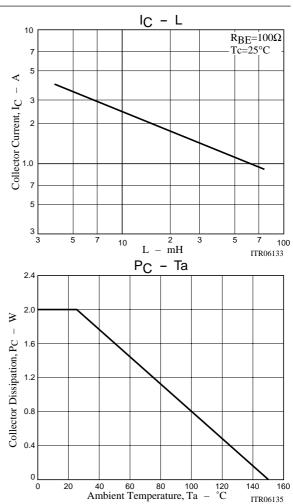




Es/b Test Circuit







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